

METHOD OF PROCESSING SUBSTRATE, METHOD OF MANUFACTURING
SEMICONDUCTOR DEVICE, PROGRAM, AND SUBSTRATE PROCESSING
APPARATUS

ABSTRACT

There is provided a technique that includes: forming a film, which contains a first element, a second element and a third element, on a substrate by performing a cycle a predetermined number of times, the cycle including performing: (a) supplying a first gas, which contains the first element and a halogen element, to the substrate; (b) supplying a second gas, which contains hydrogen and the second element that is different from the first element, to the substrate; (c) supplying a plasma-excited hydrogen-containing gas, which is different from the second gas, to the substrate; and (d) supplying a third gas, which contains the third element that is different from the first element and the second element, to the substrate, wherein (c) is performed after (a) and (b) and before (d).

Fig. 4